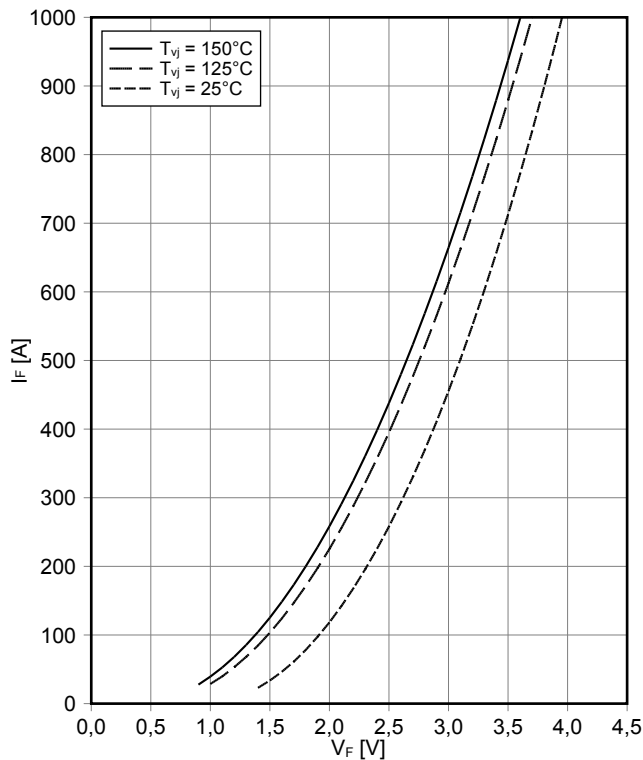


Modul / Module

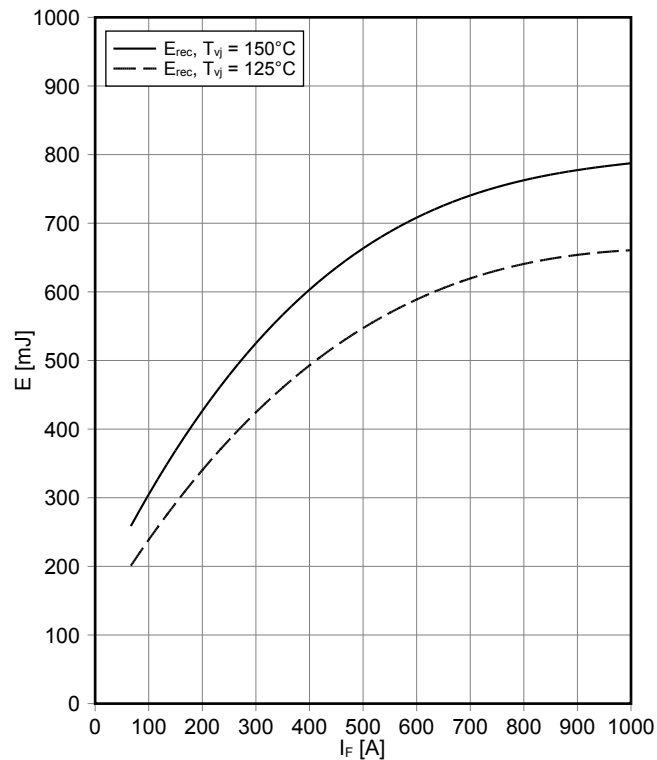
| | | | | | | |
|---|--|----------------------|------------|--------|-----------|----------|
| Isolations-Prüfspannung Isolation test voltage | RMS, f = 50 Hz, t = 1 min. | V _{ISOL} | 6,0 | | | kV |
| Teilentladungs-Aussetzspannung Partial discharge extinction voltage | RMS, f = 50 Hz, Q _{PD} ≤ 10 pC | V _{ISOL} | 2,6 | | | kV |
| Kollektor-Emitter-Gleichsperrspannung DC stability | T _{vj} = 25°C, 100 fit | V _{CE D} | 2100 | | | V |
| Material Modulgrundplatte Material of module baseplate | | | AlSiC | | | |
| Kriechstrecke Creepage distance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 32,2 | | | mm |
| Luftstrecke Clearance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 19,1 | | | mm |
| Vergleichszahl der Kriechwegbildung Comperative tracking index | | CTI | > 600 | | | |
| | | | min. | typ. | max. | |
| Modulstreuinduktivität Stray inductance module | | L _{sCE} | | 18 | | nH |
| Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip | T _c = 25°C, pro Schalter / per switch | R _{AA'+CC'} | | 0,37 | | mΩ |
| Lagertemperatur Storage temperature | | T _{stg} | -40 | | 150 | °C |
| Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting | Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note | M | 4,25 | | 5,75 | Nm |
| Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque | Schraube M4 - Montage gem. gültiger Applikationsschrift Screw M4 - Mounting according to valid application note Schraube M8 - Montage gem. gültiger Applikationsschrift Screw M8 - Mounting according to valid application note | M | 1,8 8,0 | - - | 2,1 10 | Nm Nm |
| Gewicht Weight | | G | | 800 | | g |

Dynamische Daten gelten in Verbindung mit FZ500R33HE3 Modul.
Dynamic Data valid in conjunction with FZ500R33HE3 module.

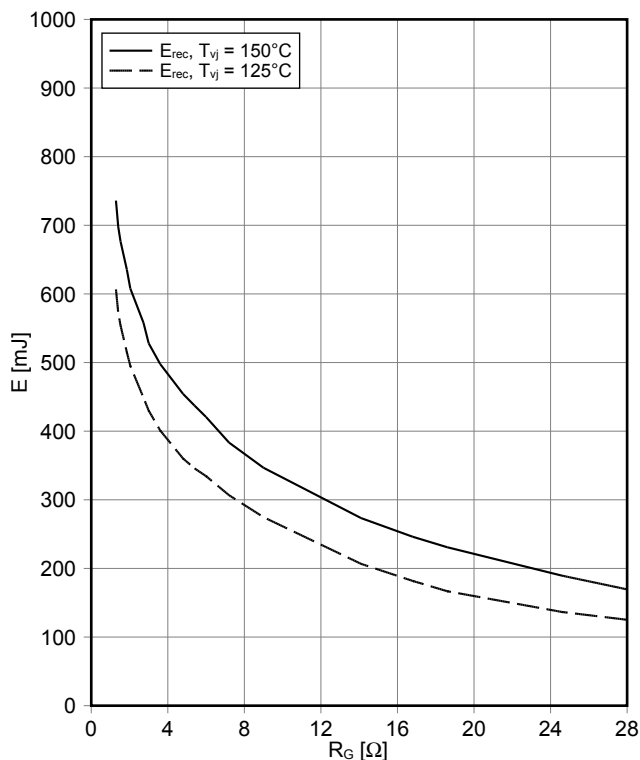
Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)
 $I_F = f(V_F)$



Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(I_F)$
 $R_{Gon} = \Omega, V_{CE} = 1800 V$



Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)
 $E_{rec} = f(R_G)$
 $I_F = 500 A, V_{CE} = 1800 V$



Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter
 $Z_{thJC} = f(t)$

